

- ◆ **COMS 2-Input NAND Gate**
- ◆ **Operating Voltage Range : 2V ~ 5.5V**
- ◆ **High Speed Operations : tpd = 2ns TYP**
- ◆ **Low Power Consumption : 1μA (max)**
- ◆ **Low ON Resistance : Ron=22Ω TYP**

### ■ Applications

- Palmtops
- Digital Equipment

### ■ General Description

The ML74UL00MRG is a 2-input CMOS NAND gate, manufactured using silicon gate CMOS fabrication.

CMOS low power circuit operation makes high speed LS-TTL operations achievable.

With a wave forming buffer connected internally, stabilized output can be achieved as the circuit offers high noise immunity.

AS the ML74UL00MRG is integrated into mini molded, SOT-23-5 package, high density mounting possible.

### ■ Features

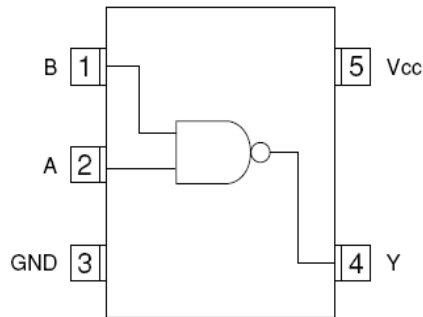
**High Speed Operation** : tpd = 2.6ns TYP

**Operating Voltage Range:** 2V ~ 5.5V

**Low Power Consumption:** 1μA (max)

**Ultra Small Package** : SOT-23-5

### ■ Pin Configuration



SOT-23-5 (TOP VIEW)

### ■ Function

INPUT		OUTPUT
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H=High level, L=Low level

### ■ Absolute Maximum Ratings

Ta=-40°C~85°C

PARAMETER	SYMBOL	RATINGS	UNITS
Power Supply Voltage	Vcc	-0.5 ~ +6.0	V
Input voltage	VIN	-0.5 ~ +6.0	V
Output Voltage	VOUT	-0.5 ~ Vcc +0.5	V
Input Diode Current	I <sub>IK</sub>	±20	mA
Output Diode current	I <sub>OK</sub>	±20	mA
Output Current	I <sub>O</sub> UT	±25	mA
Vcc, GND Current	I <sub>CC</sub> , I <sub>GND</sub>	±50	mA
Continuous Total Power Dissipation (Ta=55°C)	P <sub>d</sub>	150	mW
Storage Temperature	T <sub>stg</sub>	-65 ~ +150	°C

Note: Voltage is all Ground standardized.

### ■ Recommended Operating Conditions

PARAMETER	SYMBOL	V <sub>cc</sub> (V)	CONDITIONS	UNITS
Supply Voltage	V <sub>cc</sub>	-	2 ~ 5.5	V
Input Voltage	V <sub>IN</sub>	-	0 ~ 5.5	V
Output Voltage	V <sub>OUT</sub>	-	0 ~ V <sub>cc</sub>	V
Operating Temperature	T <sub>opr</sub>	-	-40 ~ +85	°C
Output Current	I <sub>OH</sub>	3.0	-4	mA
		4.5	-8	
	I <sub>OL</sub>	3.0	4	
		4.5	8	
Input Rise and Fall Time	tr, tf	3.3	0 ~ 100	Ns/V
		5.0	0 ~ 20	

### ■ DC Electrical Characteristics

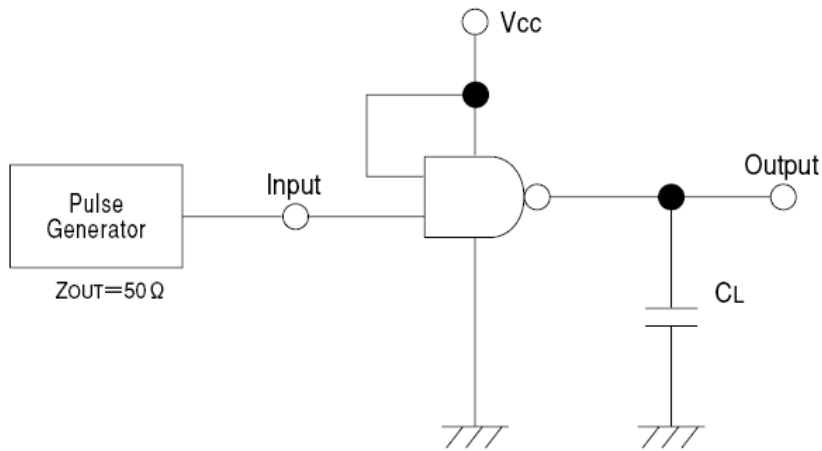
PARAMETER	SYMBOL	V <sub>cc</sub> (V)	CONDITIONS	Ta=25°C			Ta=-40~85°C		UNITS	
				MIN	TYP	MAX	MIN	MAX		
Input Voltage	V <sub>IH</sub>	2.0		1.5	-	-	1.5	-	V	
		3.0		2.1	-	-	2.1	-		
		5.5		3.85	-	-	3.85	-		
	V <sub>IL</sub>	2.0		-	-	0.5	-	0.5	V	
		3.0		-	-	0.9	-	0.9		
		5.5		-	-	1.65	-	1.65		
Output Voltage	V <sub>OH</sub>	2.0	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> =-50μA	1.9	2.0	-	1.9	-	V
		3.0			2.9	3.0	-	2.9	-	
		4.5			4.4	4.5	-	4.4	-	
		3.0			2.58	-	-	2.48	-	
		4.5			3.94	-	-	2.80	-	
	V <sub>OL</sub>	2.0	V <sub>IN</sub> =V <sub>IH</sub>	I <sub>OL</sub> =50μA	-	-	0.1	-	0.1	V
		3.0			-	-	0.1	-	0.1	
		4.5			-	-	0.1	-	0.1	
		3.0			-	-	0.36	-	0.44	
		4.5			-	-	0.36	-	0.44	
Input Current	I <sub>IN</sub>	5.5	V <sub>IN</sub> =V <sub>cc</sub> or GND	-0.1	-	0.1	-1.0	1.0	μA	
Quiescent Supply Current	I <sub>cc</sub>	5.5	V <sub>IN</sub> =V <sub>cc</sub> or GND, I <sub>OUT</sub> =0μA	-	-	1.0	-	10.0	μA	

### ■ Switching Electrical Characteristics

PARAMETER	SYMBOL	C <sub>L</sub>	V <sub>cc</sub> (V)	CONDITIONS	Ta=25°C			Ta=-40~85°C		UNITS
					MIN	TYP	MAX	MIN	MAX	
Propagation Delay Time	t <sub>PLH</sub>	15pF	3.3		-	3.7	7.9	1	9.5	ns
			5.0		-	2.7	5.5	1	6.5	
		50pF	3.3		-	5.4	11.4	1	13	ns
			5.0		-	3.6	7.5	1	8.5	
	t <sub>PHL</sub>	15pF	3.3		-	3.3	7.9	1	9.5	ns
			5.0		-	2.5	5.5	1	6.5	
		50pF	3.3		-	4.6	11.4	1	13	ns
			5.0		-	3.5	7.5	1	8.5	
Input Capacitance	C <sub>IN</sub>	-	5.0	V <sub>IN</sub> =V <sub>cc</sub> or GND	-	2	10	-	10	pF
Power Dissipation Capacitance	C <sub>pd</sub>	No Load, f=1MHz			-	9.3	-	-	-	pF

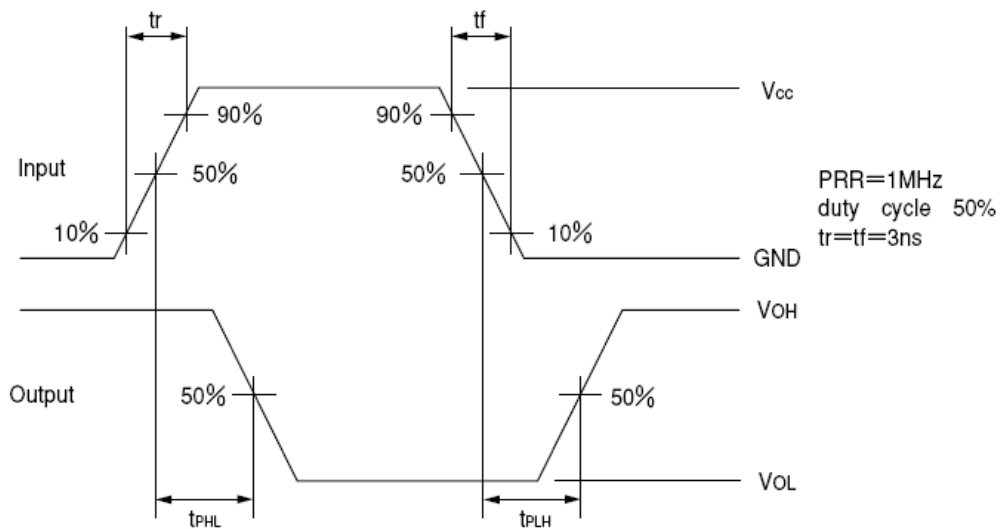
Tr=tf=3ns

## ■ Typical Application Circuit



Note: Open output when measuring supply current

## ■ Waveforms



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